

Automotive P-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	- 60
$R_{DS(on)}$ (Ω) at $V_{GS} = - 10$ V	0.0155
$R_{DS(on)}$ (Ω) at $V_{GS} = - 4.5$ V	0.0200
I_D (A)	- 50
Configuration	Single

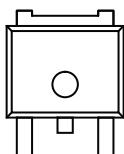


RoHS
COMPLIANT
HALOGEN
FREE

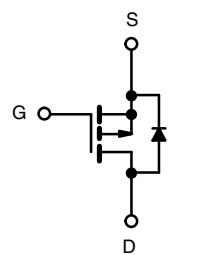
FEATURES

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R_g and UIS Tested
- AEC-Q101 Qualified
- Material categorization:
For definitions of compliance please see
www.vishay.com/doc?99912

TO-252



Top View



P-Channel MOSFET

ORDERING INFORMATION

Package	TO-252
Lead (Pb)-free and Halogen-free	SQD50P06-15L-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	- 60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^a	I_D	- 50	A
		- 38	
Continuous Source Current (Diode Conduction) ^a	I_S	- 50	
Pulsed Drain Current ^b	I_{DM}	- 200	
Single Pulse Avalanche Current	I_{AS}	- 52	mJ
Single Pulse Avalanche Energy	E_{AS}	135	
Maximum Power Dissipation ^b	P_D	136	W
		45	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	50	°C/W
Junction-to-Case (Drain)	R_{thJC}	1.1	

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).

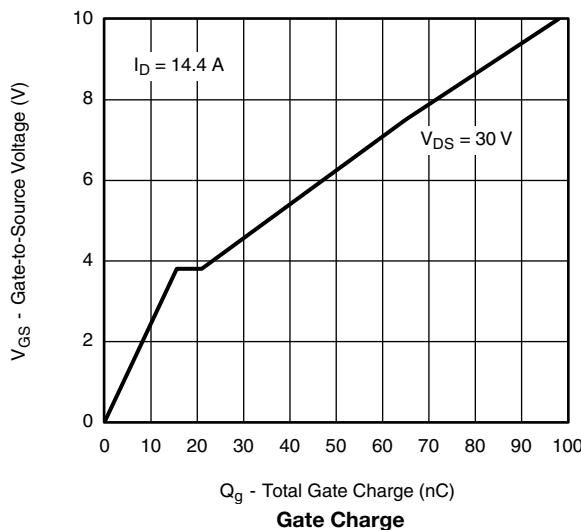
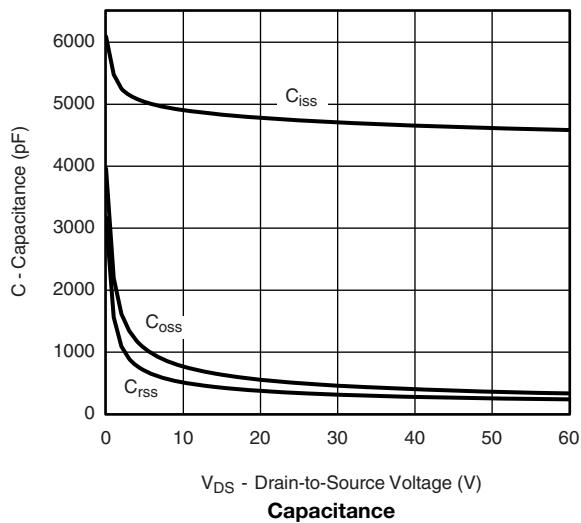
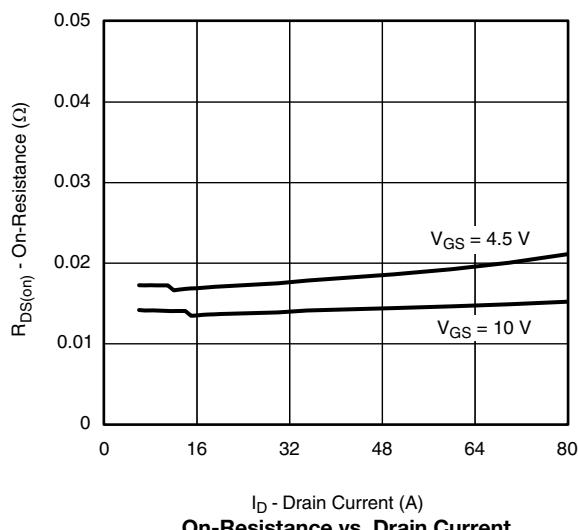
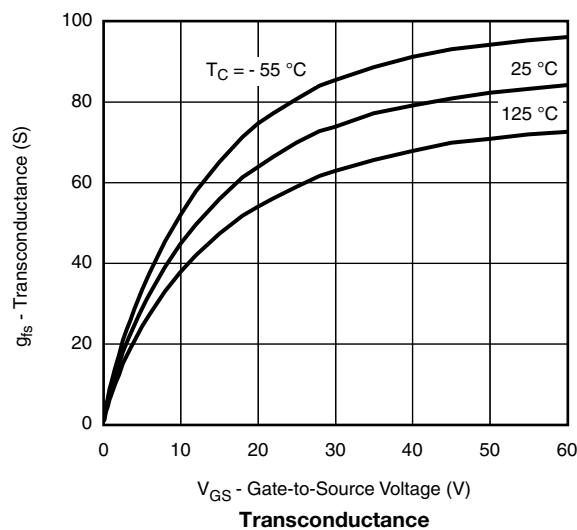
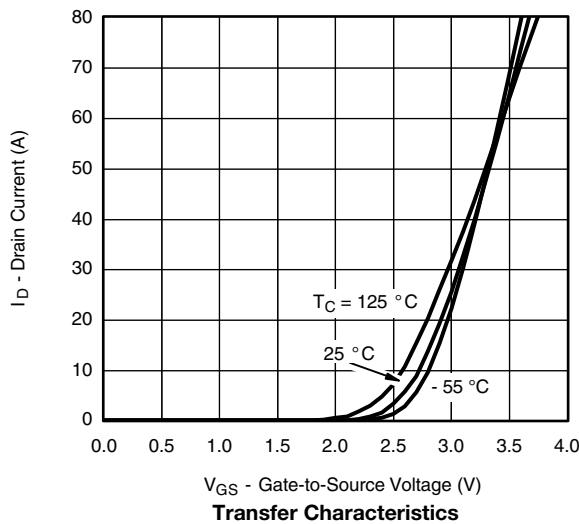
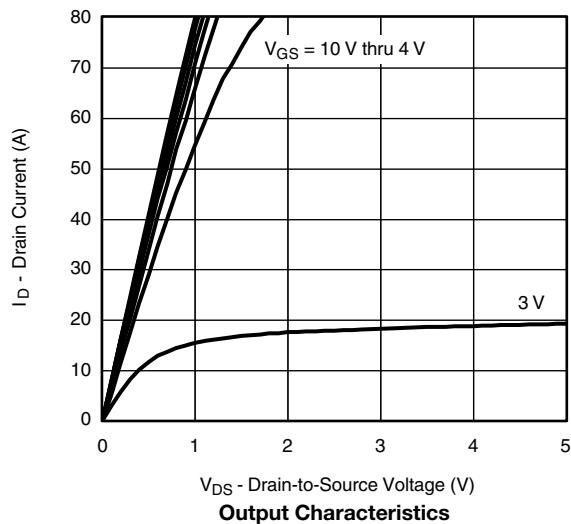
SPECIFICATIONS ($T_C = 25^\circ\text{C}$, unless otherwise noted)

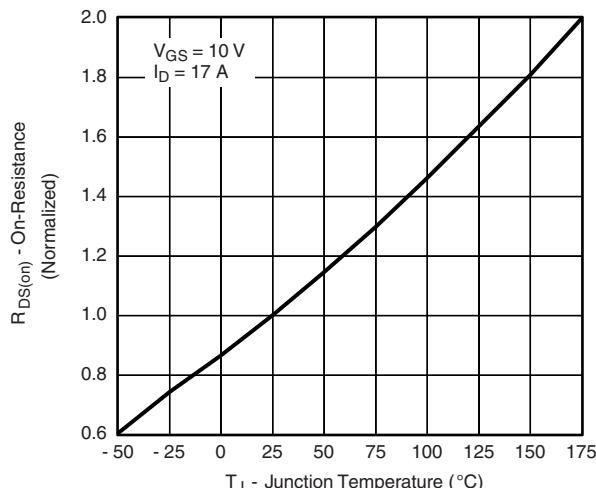
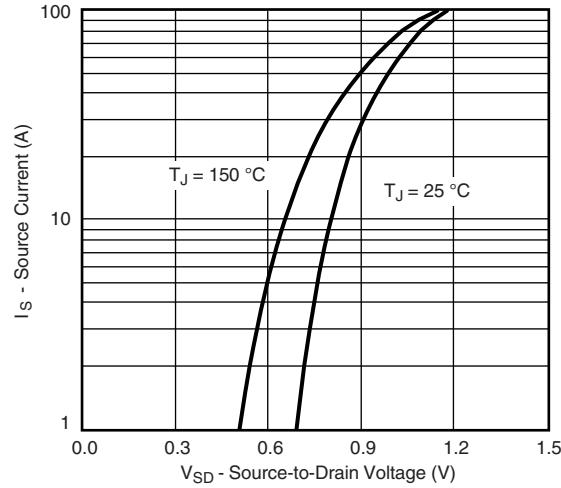
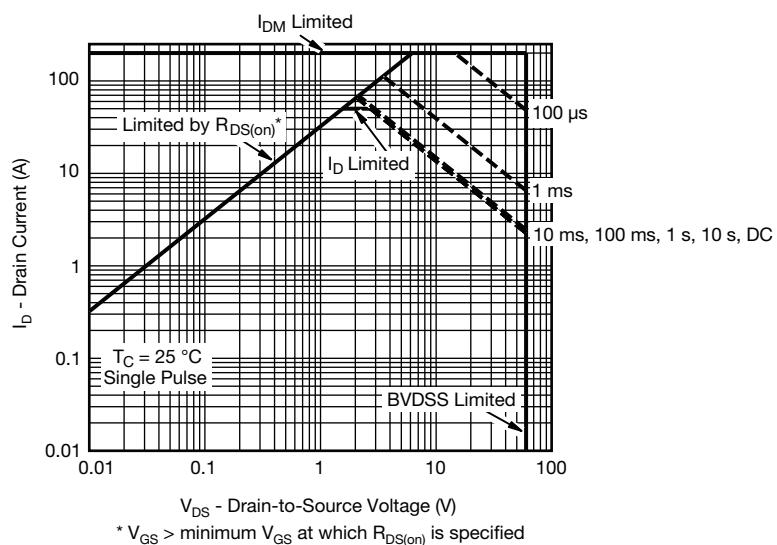
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}$, $I_D = -250 \mu\text{A}$		- 60	-	-	V	
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu\text{A}$		- 1.5	-	- 2.5		
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0 \text{ V}$	$V_{DS} = -60 \text{ V}$	-	-	- 1	μA	
		$V_{GS} = 0 \text{ V}$	$V_{DS} = -60 \text{ V}$, $T_J = 125^\circ\text{C}$	-	-	- 50		
		$V_{GS} = 0 \text{ V}$	$V_{DS} = -60 \text{ V}$, $T_J = 175^\circ\text{C}$	-	-	- 150		
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{GS} = -10 \text{ V}$	$V_{DS} \geq -5 \text{ V}$	- 50	-	-	A	
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = -10 \text{ V}$	$I_D = -17 \text{ A}$	-	0.0135	0.0155	Ω	
		$V_{GS} = -10 \text{ V}$	$I_D = -50 \text{ A}$, $T_J = 125^\circ\text{C}$	-	-	0.026		
		$V_{GS} = -10 \text{ V}$	$I_D = -50 \text{ A}$, $T_J = 175^\circ\text{C}$	-	-	0.032		
		$V_{GS} = -4.5 \text{ V}$	$I_D = -14 \text{ A}$	-	0.017	0.020		
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15 \text{ V}$, $I_D = -17 \text{ A}$		-	50	-	S	
Dynamic^b								
Input Capacitance	C_{iss}	$V_{GS} = 0 \text{ V}$	$V_{DS} = -25 \text{ V}$, $f = 1 \text{ MHz}$	-	4730	5910	pF	
Output Capacitance	C_{oss}			-	485	606		
Reverse Transfer Capacitance	C_{rss}			-	330	410		
Total Gate Charge ^c	Q_g	$V_{GS} = -10 \text{ V}$	$V_{DS} = -30 \text{ V}$, $I_D = -50 \text{ A}$	-	98	150	nC	
Gate-Source Charge ^c	Q_{gs}			-	15	23		
Gate-Drain Charge ^c	Q_{gd}			-	21	32		
Gate Resistance	R_g	$f = 1 \text{ MHz}$		1.47	2.9	4.42	Ω	
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = -30 \text{ V}$, $R_L = 0.6 \Omega$ $I_D \geq -50 \text{ A}$, $V_{GEN} = -10 \text{ V}$, $R_g = 6.0 \Omega$		-	15	18	ns	
Rise Time ^c	t_r			-	12	16		
Turn-Off Delay Time ^c	$t_{d(off)}$			-	112	125		
Fall Time ^c	t_f			-	39	48		
Source-Drain Diode Ratings and Characteristics^b								
Pulsed Current ^a	I_{SM}			-	-	- 200	A	
Forward Voltage	V_{SD}	$I_F = -50 \text{ A}$, $V_{GS} = 0 \text{ V}$		-	- 0.8	- 1.5	V	

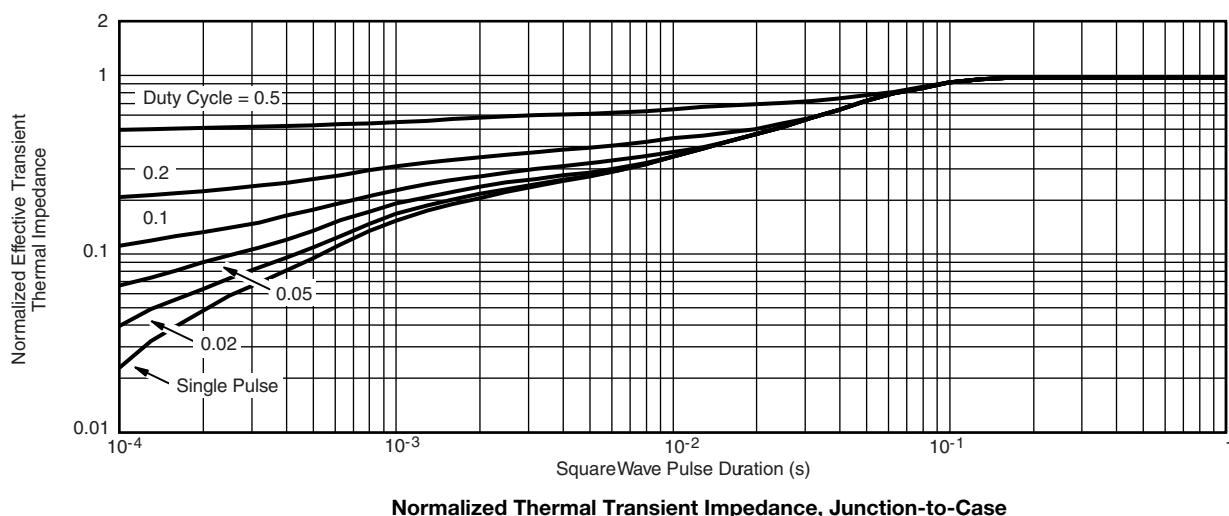
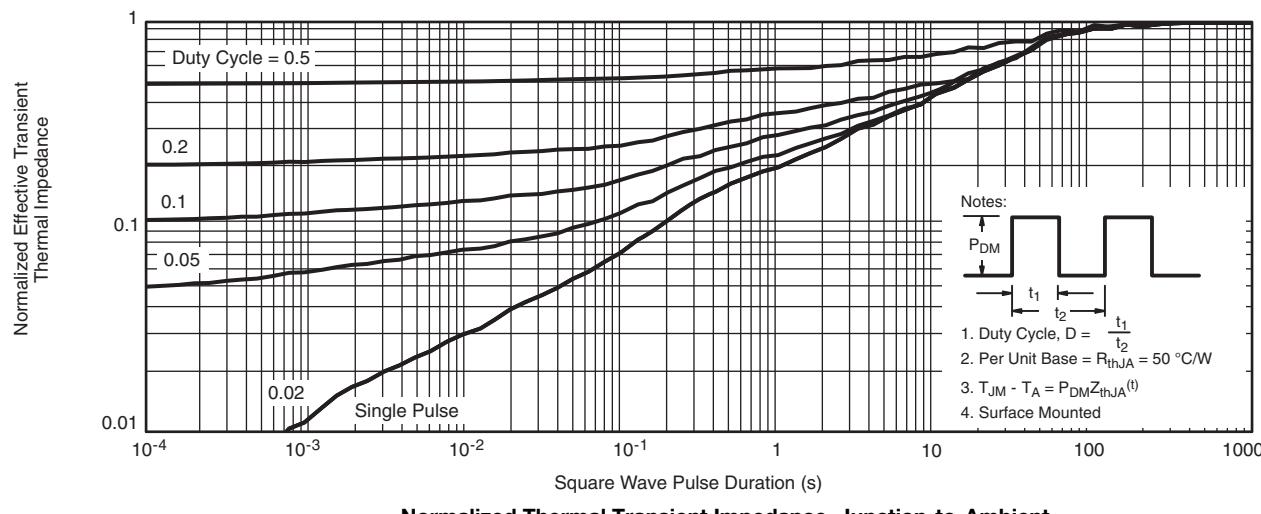
Notes

- a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)


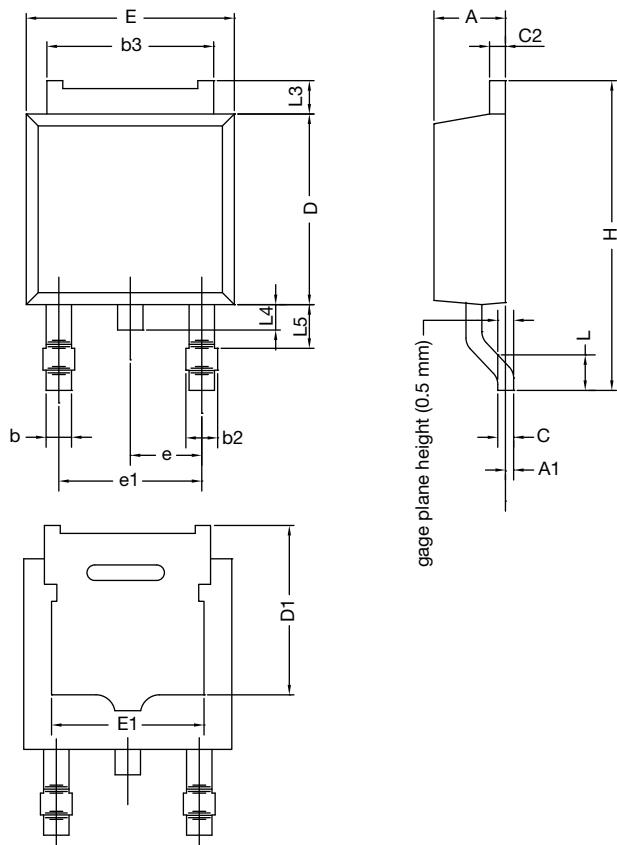
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

On-Resistance vs. Junction Temperature

Source Drain Diode Forward Voltage
THERMAL RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Safe Operating Area

THERMAL RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25°C)
 - Normalized Transient Thermal Impedance Junction to Case (25°C)
- are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?69098.

TO-252AA CASE OUTLINE

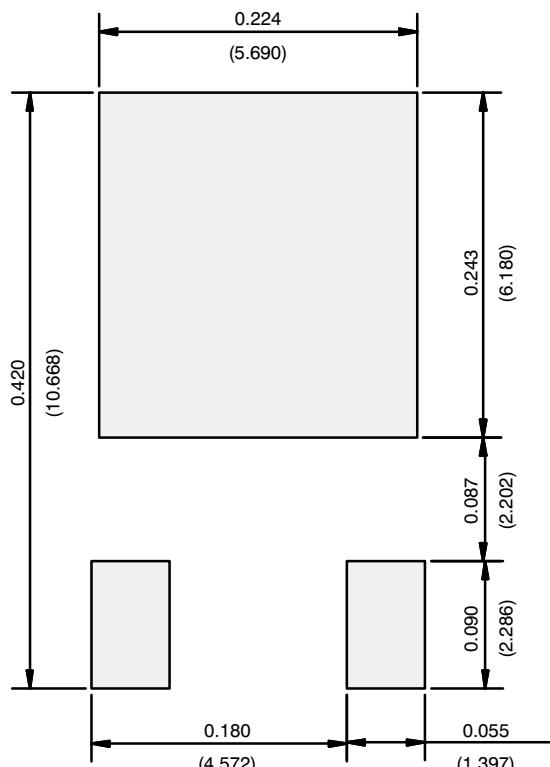


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.14	1.52	0.045	0.060

ECN: X12-0247-Rev. M, 24-Dec-12
DWG: 5347

Note

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)

Recommended Minimum Pads
Dimensions in Inches/(mm)

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- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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